TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8060-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

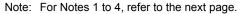
- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 17nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS}(ON) = 2.8 \text{ m}\Omega \text{ (typ.)} \text{ (V}_{GS} = 4.5 \text{ V)}$ 

- High forward transfer admittance:  $|Y_{fs}| = 141\_S$  (typ.)
- Low leakage current:  $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1.0 \text{ mA})$

## Absolute Maximum Ratings (Ta = 25°C)

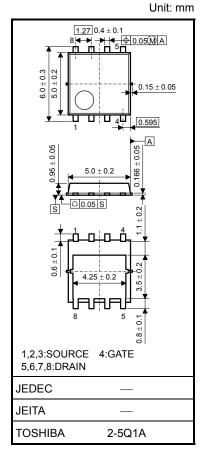
| Characte                | eristic                       | Symbol           | Rating     | Unit |
|-------------------------|-------------------------------|------------------|------------|------|
| Drain-source voltage    |                               | $V_{DSS}$        | 30         | V    |
| Drain-gate voltage (R   | $k_{GS} = 20 \text{ k}\Omega$ | $V_{DGR}$        | 30         | V    |
| Gate-source voltage     |                               | V <sub>GSS</sub> | ±20        | V    |
| Drain current           | DC (Note 1)                   | ID               | 45         | Α    |
| Drain current           | Pulsed (Note 1)               | $I_{DP}$         | 135        | Α    |
| Drain power dissipation | on (Tc = 25°C)                | $P_{D}$          | 45         | W    |
| Drain power dissipation | on $(t = 10 s)$<br>(Note 2a)  | $P_{D}$          | 2.8        | W    |
| Drain power dissipation | on (t = 10 s)<br>(Note 2b)    | P <sub>D</sub>   | 1.6        | W    |
| Single-pulse avalance   | ne energy<br>(Note 3)         | EAS              | 263        | mJ   |
| Avalanche current       |                               | I <sub>AR</sub>  | 45         | Α    |
| Repetitive avalanche    | energy<br>c = 25°C) (Note 4)  | E <sub>AR</sub>  | 3.53       | mJ   |
| Channel temperature     |                               | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature     | range                         | T <sub>stg</sub> | -55 to 150 | °C   |



Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

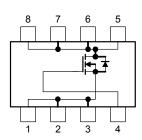
temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

### **Circuit Configuration**

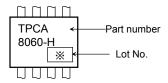




#### **Thermal Characteristics**

| Characteristic  | Symbol                 | Max  | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to case (Tc = 25°C)             | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2a) | R <sub>th (ch-a)</sub> | 44.6 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2b) | R <sub>th (ch-a)</sub> | 78.1 | °C/W |

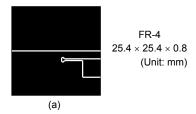
## Marking (Note 5)

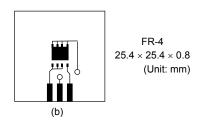


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD}=24~V,~T_{ch}=25^{\circ}C$  (initial), L = 100  $\mu H,~R_{G}=25~\Omega,~I_{AR}=45~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



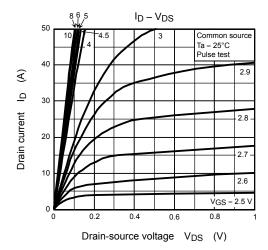


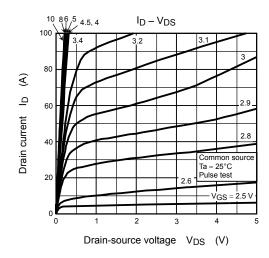
# **Electrical Characteristics (Ta = 25°C)**

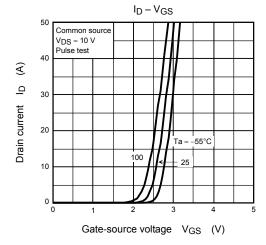
| Characteristic                                     |                | Symbol               | Test Condition   | Min      | Тур. | Max  | Unit  |
|--|----------------|----------------------|--|----------|------|------|-------|
| Gate leakage cu                                    | rrent          | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                              | _        | _    | ±100 | nA    |
| Drain cutoff curre                                 | ent            | I <sub>DSS</sub>     | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$                                  | _        | _    | 10   | μА    |
| Drain agurag bro                                   | akdowa valtago | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                                    | 30       | _    | _    | V     |
| Drain-source breakdown voltage                     |                | V (BR) DSX           | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                                  | 15 — —   |      | V    |       |
| Gate threshold v                                   | oltage         | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, I_{D} = 1.0 \text{ mA}$                                | 1.3      | _    | 2.3  | V     |
| Drain aguras ON                                    | registance     | Dec (c)              | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 22.5 A                               | _        | 2.8  | 3.9  |       |
| Drain-source ON-resistance                         |                | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22.5 A                                | _        | 2.3  | 3.4  | mΩ    |
| Forward transfer                                   | admittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 22.5 A                                | 71       | 141  | _    | S     |
| Input capacitance                                  | e              | C <sub>iss</sub>     |  | _        | 4600 | 6000 | pF    |
| Reverse transfer                                   | capacitance    | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                       | _        | 290  | 460  |       |
| Output capacitar                                   | ice            | Coss                 |  | _        | 860  | _    |       |
| Gate resistance                                    |                | rg                   | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                       | <u> </u> |      | 1.5  | Ω     |
| Switching time                                     | Rise time      | t <sub>r</sub>       | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz  V <sub>GS</sub> 10 V | _        | 5.1  | _    | ns ns |
|  | Turn-on time   | t <sub>on</sub>      |  | _        | 16   | _    |       |
|  | Fall time      | t <sub>f</sub>       |  | _        | 8.5  | _    |       |
|  | Turn-off time  | t <sub>off</sub>     | $V_{DD} \approx 15 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$           | _        | 52   | _    |       |
| Total gate charge<br>(gate-source plus gate-drain) |                | 0                    | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$       | _        | 66   | _    |       |
|  |                | $Q_g$                | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 45 \text{ A}$        |          | 34   | _    |       |
| Gate-source charge 1                               |                | Q <sub>gs1</sub>     | V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 45 A          | _        | 15   | _    | nC    |
| Gate-drain ("Miller") charge                       |                | Q <sub>gd</sub>      |  |          | 9.9  | _    |       |
| Gate switch charge                                 |                | Q <sub>SW</sub>      |  |          | 17   | _    |       |

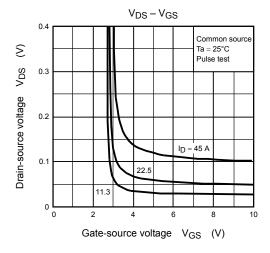
# Source-Drain Ratings and Characteristics (Ta = 25°C)

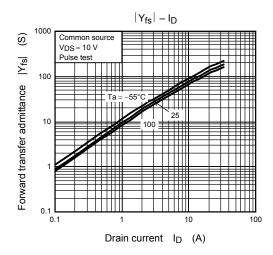
| Characteristic          |       | Symbol   | Test Condition   | Min   | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|---|------|-----|------|---|
| Drain reverse current   | Pulse | (Note 1) | I <sub>DRP</sub> | _   | _    | _   | 135  | Α |
| Forward voltage (diode) |       |          | V <sub>DSF</sub> | I <sub>DR</sub> = 45 A, V <sub>GS</sub> = 0 V | _    | _   | -1.2 | V |

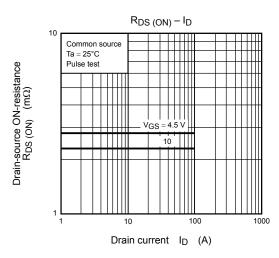




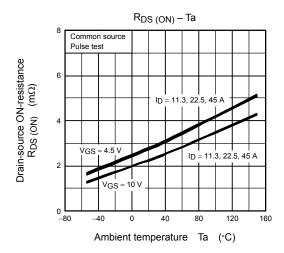


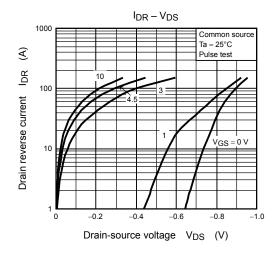


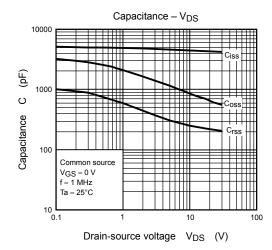


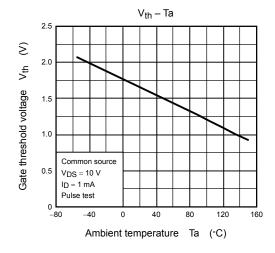


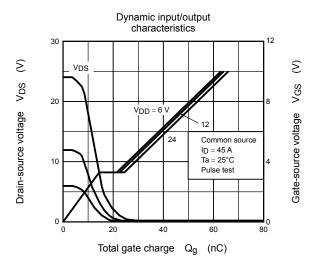
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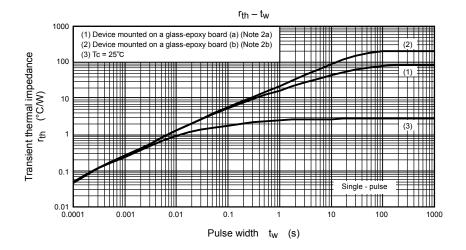


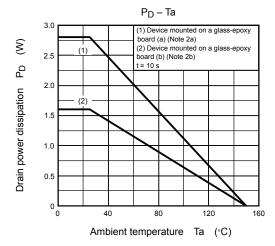


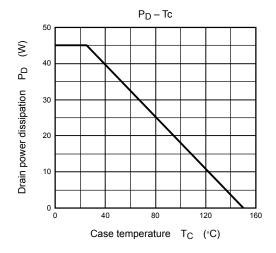


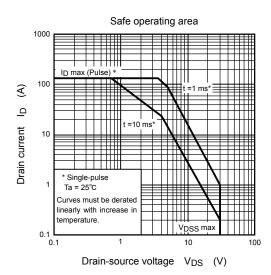


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